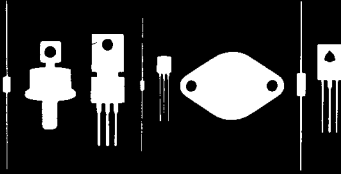


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148-B Lamar Street
West Babylon, New York 11704



SE9303 SE9304 SE9305 NPN
SE9403 SE9404 SE9405 PNP

SILICON POWER DARLINGTON
COMPLEMENTARY TRANSISTORS

JEDEC TO-3 CASE

DESCRIPTION

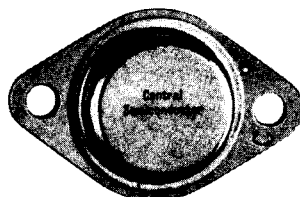
The CENTRAL SEMICONDUCTOR SE9303, SE9403 Series Types are Complementary Silicon Power Darlingtons designed for audio amplifier and power linear and switching applications.

MAXIMUM RATINGS ($T_C=25^{\circ}C$)

	SYMBOL	SE9303 SE9403	SE9304 SE9404	SE9305 SE9405	UNIT
Collector-Base Voltage	V_{CB0}	60	80	100	V
Collector-Emitter Voltage	V_{CE0}	60	80	100	V
Emitter-Base Voltage	V_{EB0}	5.0	5.0	5.0	V
Collector Current	I_C	10	10	10	A
Power Dissipation	PD	100	100	100	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 TO +200			$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}C$)

SYMBOL	TEST CONDITIONS	SE9303 SE9403		SE9304 SE9404		SE9305 SE9405		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CE}=\text{Rated } V_{CE0}$		200		200		200	μA
I_{CEO}	$V_{CE}=\frac{1}{2} \text{ Rated } V_{CE0}$		500		500		500	μA
I_{EBO}	$V_{EB}=5.0V$		4.0		4.0		4.0	mA
BV_{CE0}	$I_C=100mA$	60		80		100		V
$V_{CE(SAT)}$	$I_C=4.0A, I_B=16mA$		2.0		2.0		2.0	V
$V_{CE(SAT)}$	$I_C=7.5A, I_B=150mA$		2.5		2.5		2.5	V
$V_{BE(ON)}$	$V_{CE}=3.0V, I_C=4.0A$		2.5		2.5		2.5	V
$V_{BE(ON)}$	$V_{CE}=3.0V, I_C=7.5A$		3.0		3.0		3.0	V
h_{FE}	$V_{CE}=3.0V, I_C=1.0A$	750		750		750		-
h_{FE}	$V_{CE}=3.0V, I_C=4.0A$	1000		1000		1000		-
h_{FE}	$V_{CE}=3.0V, I_C=7.5A$	100		100		100		-
f_T	$V_{CE}=3.0V, I_C=4.0A, f=1.0MHz$	1.0		1.0		1.0		MHz



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